Department of Chemical Engineering, IIT Kharagpur
Microscale Transport Process (CH 62039) Mid-Semester Examination, Autumn 2015-16

Microscale Transport Process (CH 02039) Wild-Semester Examination, Autumn 2013-B.Tech/Dual 4th year, M.Tech 1st year, R.S. (Total students 68), Total marks 30, Duration 2 hours

O1. A major recent research effort is directed towards cooling of hot spots utilizing change-of-phase heat transfer from microgrooved surfaces.

- Mention very briefly the pertinent issue in the selection of channel dimensions for a specific process and what strategy can be used to increase the flow rate and to distribute it properly in a compact device.
- Sketch the variation of pressure drop with volumetric flow rate in a microchannel citing proper reasons.
- Two liquids are being pumped through a micrchannel at the same volumetric rate with many bends and obstructions in the flow-path. The viscosity of the second liquid is 2.5 times that of the first liquid. State with reasons the difference in the readings of a pressure drop measuring device attached to the microchannel for these two liquids.
- Can you suggest (with proper reasons) any surface modification strategy to reduce the problem of higher pressure drop in such devices?
   2+1+1+1 = 5 Marks

Q2. Starting with the Augmented Young-Laplace equation, prove that for an evaporating, curved thin film the flow towards the contact line (from the capillary meniscus region) is sustained by capillary pressure gradient and disjoining pressure.

2 Marks

3. Based on a differential volume element of a liquid in a triangular grove, derive the governing equation of flow and cite the significances of each term.

3 Marks

Q4.

j) Mention the basic steps involved in converting a laboratory scale process to microstructured

أنز) State how dilute and dense gases behave when the system size is reduced gradually.

2+1=3 Marks

## Q5. Write within two sentences the difference between

- i) anodic bonding and fusion bonding
- ii) u-stereolithography and photolithography
- iii) casting and molding
- iv) molding and microinjection
- v) cytotoxic and biocompatible
- vi) press-fit interconnect and glued interconnect
- vii) plastic coupler and integrated 'O' ring
- viii) silicon and glass in connection with crystalinity
- ix) silicon wet etching and glass wet etching
- x) positive resist and negative resist
- xi) physical dry etching and chemical dry etching
- xii) isotropic and anisotropic etching
- xiii) reactive ion etching and DRIE
- xiv) thermal evaporation and sputtering
- xv) film-dewetting and post-exposure baking of resist film
- xvi) molding in closed capillary and in open capillary
- xvii) use of PDMS and PMMA in microfabrication
- xviii) diffusion and dispersion
- xix) use of vacuum in spin coater chuck and in plasma chamber
- xx) T sensor and H filter
- xxi) valve action through hydrophoblic layer and hydrogel layer
- xxii) capillary pumping and pressure driven pumping

22×0.5=11 Marks

<u>O6.</u> A horizontal capillary of internal diameter d is to be filled by a liquid of viscosity  $\mu$  solely by capillary force. Do you expect the velocity of the liquid front in the tube to increase or decrease with time / progression? Write down the Poiseuille's equation for fully developed flow, where pressure gradient is expressed in terms of surface tension force. Assume the surface tension and contact angle as  $\sigma$  and  $\theta$  respectively. Consider the initial liquid meniscus position in the channel as  $L_0$ . Obtain the distance traveled by the liquid meniscus as function of time, and  $\sigma$ ,  $\theta$ ,  $\mu$ , d.

O7. Write down the assumptions, governing equations, and initial and boundary conditions employed in theorizing Taylor dispersion.

2 Marks

Q8. Define mixing quality and mixing effectiveness in a passive mixer.

2 Marks

## Useful relations

$$\sigma = \pi d^2 \Lambda = \frac{1}{\sqrt{2}n\sigma} Kn = \frac{\Lambda}{L} \Lambda p = \left(C_f \frac{l}{d_h} + \zeta \operatorname{Re}\right) \frac{\rho v^2 \operatorname{Re}}{2 d_h^2}$$

$$\Pi = \frac{-\overline{A}}{\delta^{3}} ; \delta < 50nm \qquad \Delta p = \left(C_{f} \eta l + \zeta \frac{V}{N}\right) \frac{\rho}{2} \frac{V}{N d_{h}^{4}}$$

$$= -\frac{B}{\delta^{4}} ; \delta > 50nm \qquad \Delta p = \left(C_{f} v \frac{l}{d_{h}} + \zeta d_{h} w\right) \frac{\rho}{2} \frac{\overline{w}}{d_{h}} = C_{f} \frac{\eta l}{2 d_{h}} w + \zeta \frac{\rho}{2} \overline{w}^{2}$$

$$\Delta P = P_i - P_v = -\sigma K - \Pi$$

$$\omega = \frac{1}{\lambda_{\rm D}} = \sqrt{\frac{e^2 \Sigma_i n_i z_i^2}{\epsilon \epsilon_{\rm o} k_{\rm B} T}}$$